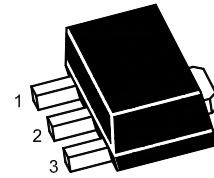


PNP SILICON EPITAXIAL POWER TRANSISTOR

These devices are intended for use in audio frequency power amplifier and low speed switching applications



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CB0}	40	V
Collector Emitter Voltage	-V _{CEO}	30	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	3	A
Peak Collector Current (t = 10 ms)	-I _{CP}	7	A
Base Current	-I _B	0.6	A
Total Power Dissipation @ T _a = 25 °C	P _D	1	W
Total Power Dissipation @ T _c = 25 °C	P _D	10	W
Operating and Storage Junction Temperature Range	T _j , T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at -V _{CE} = 2 V, -I _C = 20 mA at -V _{CE} = 2 V, -I _C = 1 A Current Gain Group	R	30	-	-	-
	Q	60	-	120	-
	P	100	-	200	-
	E	160	-	320	-
			200	-	400
Collector Base Cutoff Current at -V _{CB} = 30 V	-I _{CB0}	-	-	1	μA
Emitter Base Cutoff Current at -V _{EB} = 3 V	-I _{EBO}	-	-	1	μA
Collector Base Breakdown Voltage at -I _C = 1 mA	-V _{(BR)CBO}	40	-	-	V
Collector Emitter Breakdown Voltage at -I _C = 1 mA	-V _{(BR)CEO}	30	-	-	V
Emitter Base Breakdown Voltage at -I _E = 1 mA	-V _{(BR)EBO}	5	-	-	V
Collector Emitter Saturation Voltage at -I _C = 2 A, -I _B = 200 mA	-V _{CE(sat)}	-	-	0.5	V
Base Emitter Saturation Voltage at -I _C = 2 A, -I _B = 200 mA	-V _{BE(sat)}	-	-	2	V
Current Gain Bandwidth Product at -V _{CE} = 5 V, -I _C = 100 mA,	f _T	-	80	-	MHz
Output Capacitance at -V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	55	-	pF